

	Type	L #	Hits	Search Text	DBs	Time Stamp
2	BRS	L7	58617	(nitrogen or nitrogen-contain\$4 or N2-contain\$4 or nitridat\$5 or nitrifying or nitrified or nitridiz\$4 or N?su\$3) same (thickness or angstrom or nm or nanometer or nano-meter or nanometre)	USPAT; US-PG PUB; EPO; JPO; DERW ENT; IBM_TD B	2002/10/25 16:14
3	BRS	L14	185355	(SiO2 or SiO?sub\$2 or oxide or dioxide or oxidat\$4 or oxidiz\$5) same (thickness or angstrom or nm or nanometer or nano-meter or nanometre)	USPAT; US-PG PUB; EPO; JPO; DERW ENT; IBM_TD B	2002/10/25 16:18
4	BRS	L21	16071	(nitrogen or N-atom or N-ion or nitrogen-atom or nitrogen-ion) near20 (dispers\$4 or diffus\$4)	USPAT; US-PG PUB; EPO; JPO; DERW ENT; IBM_TD B	2002/10/25 16:19
5	BRS	L28	1537	7 and 14 and 21	USPAT; US-PG PUB; EPO; JPO; DERW ENT; IBM_TD B	2002/10/25 16:17
11	BRS	L70	2158	(nitrogen or N-atom or N-ion or nitrogen-atom or nitrogen-ion) near20 (dispers\$4 or diffus\$4) near20 (oxide or dioxide or SiO2 or SiO?su\$3 or oxide-region)	USPAT; US-PG PUB; EPO; JPO; DERW ENT; IBM_TD B	2002/10/25 16:22

	Type	L #	Hits	Search Text	DBs	Time Stamp
12	BRS	L77	319	7 and 14 and 70 and semiconductor	USPAT; US-PG PUB; EPO; JPO; DERW ENT; IBM_TD B	2002/10/25 16:22

	Type	L #	Hits	Search Text	DBs	Time Stamp
1	BRS	L1	59411	(nitrogen or nitrogen-contain\$4 or N2-contain\$4 or nitridat\$5 or nitrifying or nitrified or nitridiz\$4 or N?su?\$3) same (thickness or angstrom or nm or nanometer or nano-meter)	USPAT; US-PG PUB; EPO; JPO; DERW ENT; IBM_TDB	2002/10/25 12:21
2	BRS	L8	185263	(SiO2 or SiO?sub\$2 or oxide or dioxide or oxidat\$4 or oxidiz\$5) same (thickness or angstrom or nm or nanometer or nano-meter)	USPAT; US-PG PUB; EPO; JPO; DERW ENT; IBM_TDB	2002/10/25 12:16
3	BRS	L15	18689	1 and 8 and semiconductor	USPAT; US-PG PUB; EPO; JPO; DERW ENT; IBM_TDB	2002/10/25 12:10
4	BRS	L22	21320	(nitrogen or nitrogen-contain\$4 or N2-contain\$4 or nitridat\$5 or nitrifying or nitrified or nitridiz\$4 or N?su?\$3) near20 (thickness or angstrom or nm or nanometer or nano-meter)	USPAT; US-PG PUB; EPO; JPO; DERW ENT; IBM_TDB	2002/10/25 12:13
5	BRS	L29	106276	(SiO2 or SiO?sub\$2 or oxide or dioxide or oxidat\$4 or oxidiz\$5) near20 (thickness or angstrom or nm or nanometer or nano-meter)	USPAT; US-PG PUB; EPO; JPO; DERW ENT; IBM_TDB	2002/10/25 12:15

	Type	L #	Hits	Search Text	DBs	Time Stamp
6	BRS	L36	6727	22 and 29 and (semiconductor or semiconductor-device)	USPAT; US-PG PUB; EPO; JPO; DERW ENT; IBM_TD B	2002/10/25 12:16
7	BRS	L43	5683	36 and (grow\$4 or oxidat\$4 or oxidiz\$5)	USPAT; US-PG PUB; EPO; JPO; DERW ENT; IBM_TD B	2002/10/25 12:17
8	BRS	L50	4892	36 and ((grow\$4 or oxidat\$4 or oxidiz\$5) same (SiO2 or SiO?sub\$2 or oxide or dioxide))	USPAT; US-PG PUB; EPO; JPO; DERW ENT; IBM_TD B	2002/10/25 12:20
9	BRS	L57	2802	36 and ((grow\$4 or oxidat\$4 or oxidiz\$5) same (SiO2 or SiO?sub\$2 or oxide or dioxide) same (nitride or nitrogen or nitrogen-contain\$4 or nitridat\$5 or nitridiz\$4 or nitrifying))	USPAT; US-PG PUB; EPO; JPO; DERW ENT; IBM_TD B	2002/10/25 12:22